

FDD5N50F

N-Channel MOSFET, FRFET

500V, 3.5A, 1.55Ω

Features

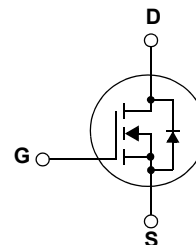
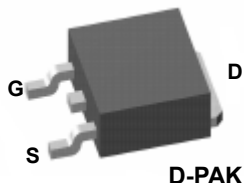
- $R_{DS(on)} = 1.25\Omega$ (Typ.) @ $V_{GS} = 10V, I_D = 1.75A$
- Low gate charge (Typ. 11nC)
- Low C_{RSS} (Typ. 5pF)
- Fast switching
- 100% avalanche tested
- Improved dv/dt capability
- RoHS compliant



Description

These N-Channel enhancement mode power field effect transistors are produced using Fairchild's proprietary, planar stripe, DMOS technology.

This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pluse in the avalanche and commutation mode. These devices are well suited for high efficient switched mode power supplies and active power factor-correction.



MOSFET Maximum Ratings $T_C = 25^\circ C$ unless otherwise noted*

Symbol	Parameter	Ratings	Units
V_{DSS}	Drain to Source Voltage	500	V
V_{GSS}	Gate to Source Voltage	±30	V
I_D	Drain Current	-Continuous ($T_C = 25^\circ C$)	3.5
		-Continuous ($T_C = 100^\circ C$)	2.1
I_{DM}	Drain Current	- Pulsed (Note 1)	14
E_{AS}	Single Pulsed Avalanche Energy	(Note 2)	257
I_{AR}	Avalanche Current	(Note 1)	3.5
E_{AR}	Repetitive Avalanche Energy	(Note 1)	4
dv/dt	Peak Diode Recovery dv/dt	(Note 3)	4.5
P_D	Power Dissipation	($T_C = 25^\circ C$)	40
		- Derate above $25^\circ C$	0.3
T_J, T_{STG}	Operating and Storage Temperature Range	-55 to +150	$^\circ C$
T_L	Maximum Lead Temperature for Soldering Purpose, 1/8" from Case for 5 Seconds	300	$^\circ C$

Thermal Characteristics

Symbol	Parameter	Ratings	Units
$R_{\theta JC}$	Thermal Resistance, Junction to Case	1.4	$^\circ C/W$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	110	

Package Marking and Ordering Information $T_C = 25^\circ\text{C}$ unless otherwise noted

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FDD5N50F	FDD5N50FTM	D-PAK	380mm	16mm	2500
FDD5N50F	FDD5N50FTF	D-PAK	380mm	16mm	2000

Electrical Characteristics

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
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Off Characteristics

BV_{DSS}	Drain to Source Breakdown Voltage	$I_D = 250\mu\text{A}, V_{GS} = 0\text{V}, T_J = 25^\circ\text{C}$	500	-	-	V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	$I_D = 250\mu\text{A}$, Referenced to 25°C	-	0.6	-	$\text{V}/^\circ\text{C}$
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 500\text{V}, V_{GS} = 0\text{V}$ $V_{DS} = 400\text{V}, T_C = 125^\circ\text{C}$	-	-	10 100	μA
I_{GSS}	Gate to Body Leakage Current	$V_{GS} = \pm 30\text{V}, V_{DS} = 0\text{V}$	-	-	± 100	nA

On Characteristics

$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS} = V_{DS}, I_D = 250\mu\text{A}$	3.0	-	5.0	V
$R_{DS(on)}$	Static Drain to Source On Resistance	$V_{GS} = 10\text{V}, I_D = 1.75\text{A}$	-	1.25	1.55	Ω
g_{FS}	Forward Transconductance	$V_{DS} = 20\text{V}, I_D = 1.75\text{A}$ (Note 4)	-	4.3	-	S

Dynamic Characteristics

C_{iss}	Input Capacitance	$V_{DS} = 25\text{V}, V_{GS} = 0\text{V}$ $f = 1\text{MHz}$	-	490	650	pF
C_{oss}	Output Capacitance		-	66	88	pF
C_{rss}	Reverse Transfer Capacitance		-	5	7.5	pF
$Q_{g(tot)}$	Total Gate Charge at 10V	$V_{DS} = 400\text{V}, I_D = 5\text{A}$ $V_{GS} = 10\text{V}$	-	11	15	nC
Q_{gs}	Gate to Source Gate Charge		-	3	-	nC
Q_{gd}	Gate to Drain "Miller" Charge		-	5	-	nC

Switching Characteristics

$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 250\text{V}, I_D = 5\text{A}$ $R_G = 25\Omega$	-	13	36	ns
t_r	Turn-On Rise Time		-	22	54	ns
$t_{d(off)}$	Turn-Off Delay Time		-	28	66	ns
t_f	Turn-Off Fall Time		-	20	50	ns

Drain-Source Diode Characteristics

I_S	Maximum Continuous Drain to Source Diode Forward Current	-	-	3.5	A	
I_{SM}	Maximum Pulsed Drain to Source Diode Forward Current	-	-	14	A	
V_{SD}	Drain to Source Diode Forward Voltage	$V_{GS} = 0\text{V}, I_{SD} = 3.5\text{A}$	-	-	1.5	V
t_{rr}	Reverse Recovery Time	$V_{GS} = 0\text{V}, I_{SD} = 5\text{A}$	-	65	-	ns
Q_{rr}	Reverse Recovery Charge	$di_F/dt = 100\text{A}/\mu\text{s}$ (Note 4)	-	0.120	-	μC

Notes:

- 1: Repetitive Rating: Pulse width limited by maximum junction temperature
- 2: $L = 42\text{mH}, I_{AS} = 3.5\text{A}, V_{DD} = 50\text{V}, R_G = 25\Omega$, Starting $T_J = 25^\circ\text{C}$
- 3: $I_{SD} \leq 3.5\text{A}, di/dt \leq 200\text{A}/\mu\text{s}, V_{DD} \leq BV_{DSS}$, Starting $T_J = 25^\circ\text{C}$
- 4: Pulse Test: Pulse width $\leq 300\mu\text{s}$, Duty Cycle $\leq 2\%$
- 5: Essentially Independent of Operating Temperature Typical Characteristics

Typical Performance Characteristics

Figure 1. On-Region Characteristics

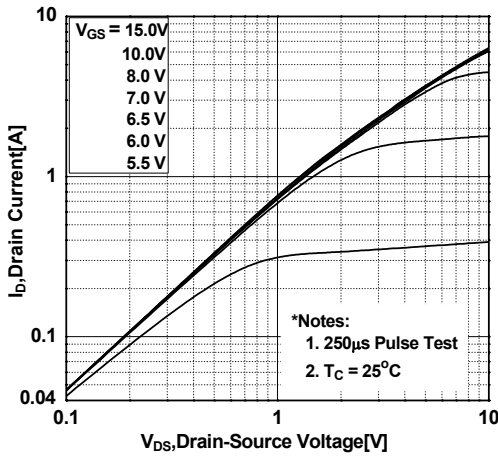


Figure 2. Transfer Characteristics

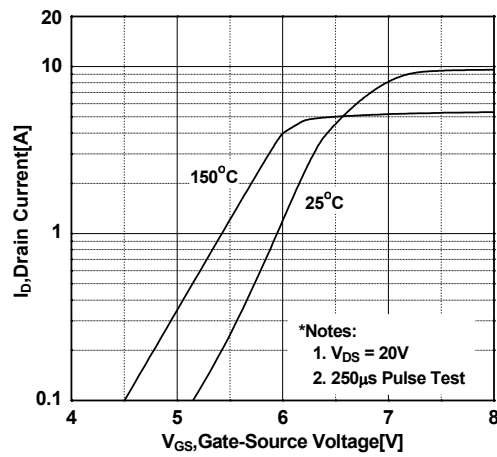


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

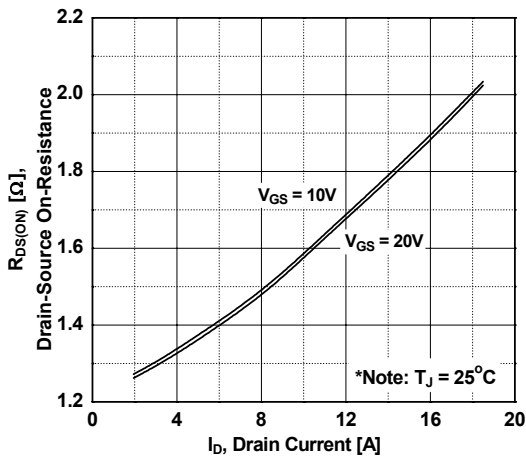


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

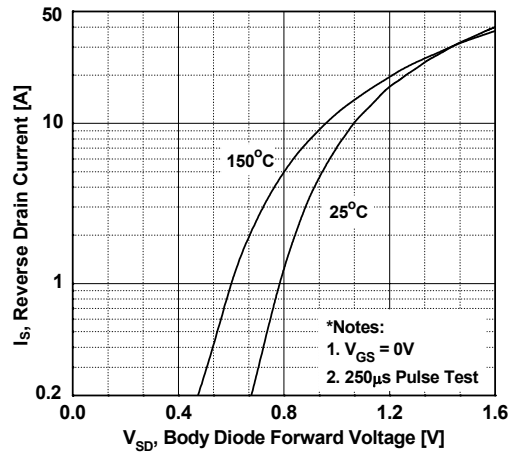


Figure 5. Capacitance Characteristics

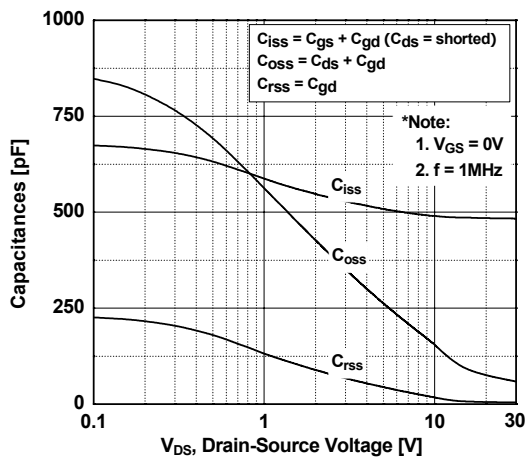
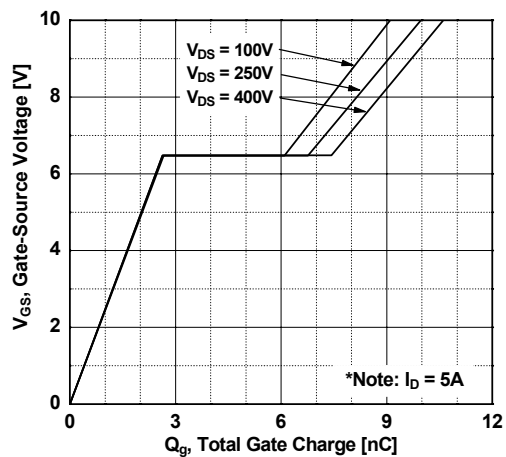


Figure 6. Gate Charge Characteristics



Typical Performance Characteristics (Continued)

Figure 7. Breakdown Voltage Variation vs. Temperature

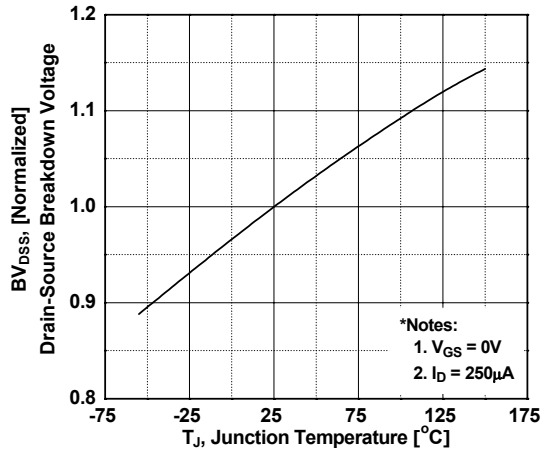


Figure 8. Maximum Safe Operating Area

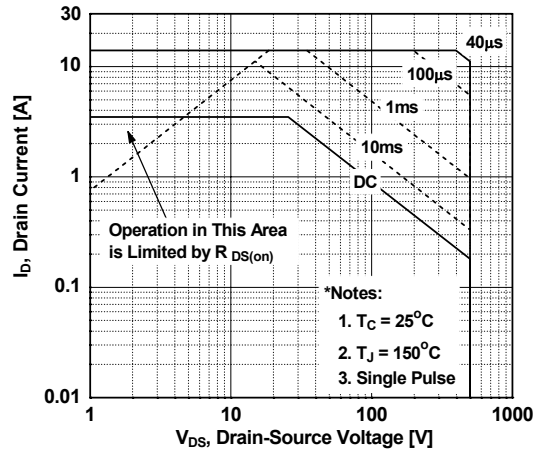


Figure 9. Maximum Drain Current

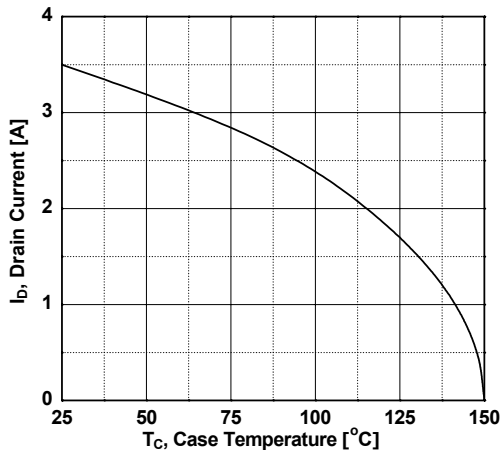
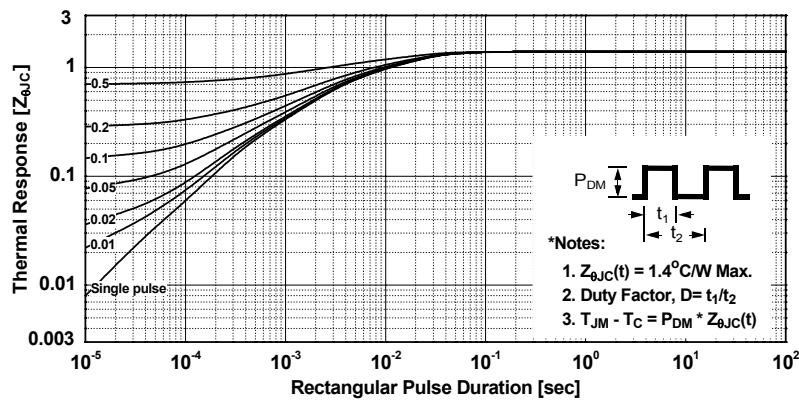
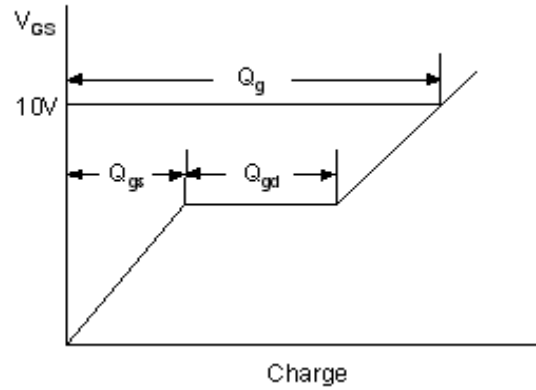
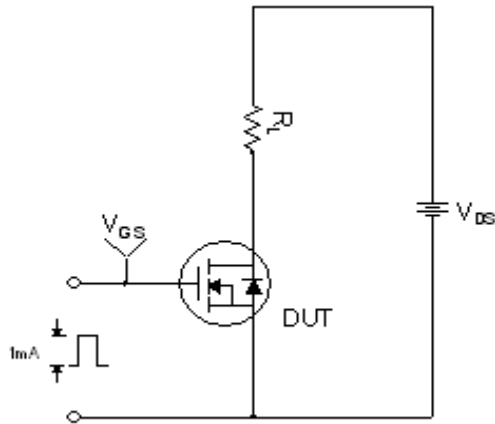


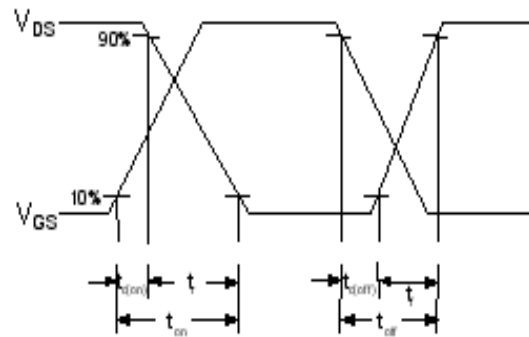
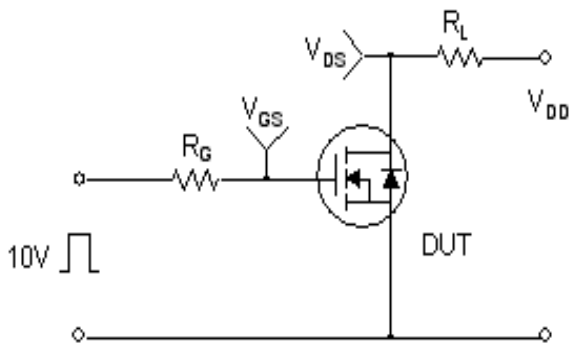
Figure 10. Transient Thermal Response Curve



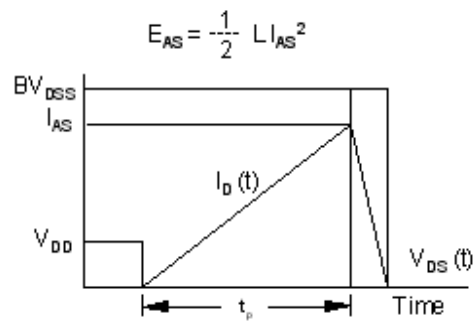
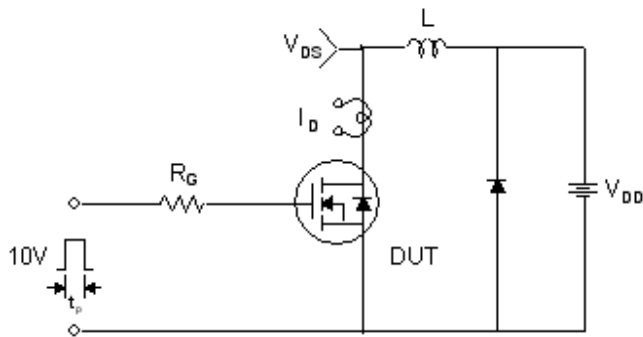
Gate Charge Test Circuit & Waveform



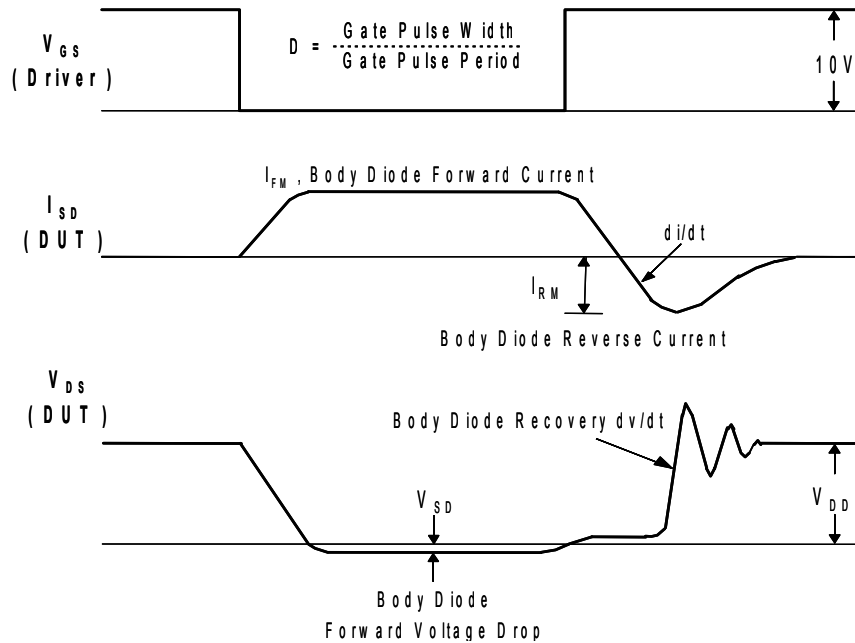
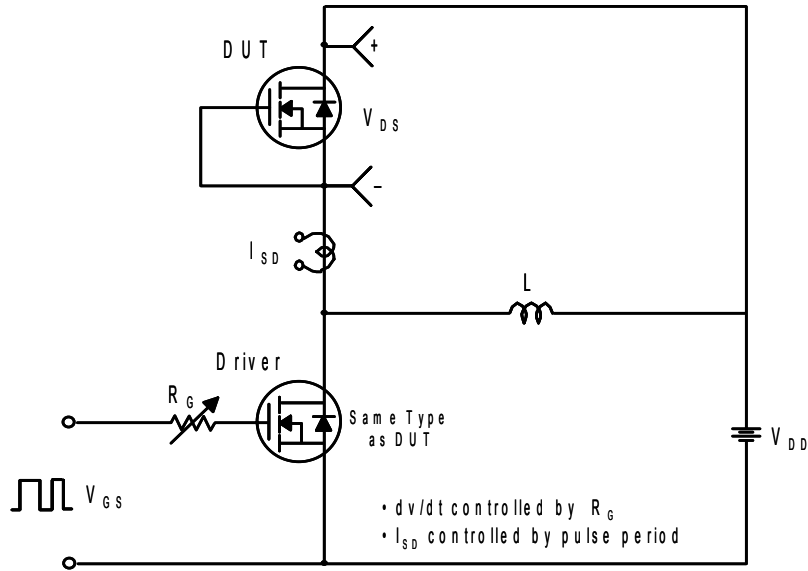
Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching Test Circuit & Waveforms

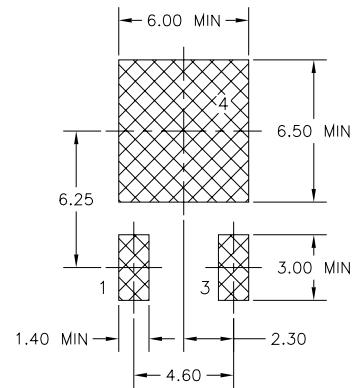
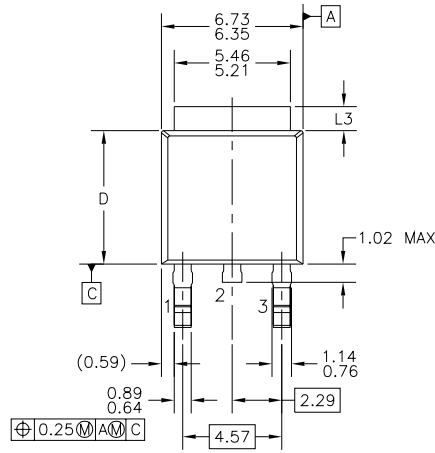


Peak Diode Recovery dv/dt Test Circuit & Waveforms

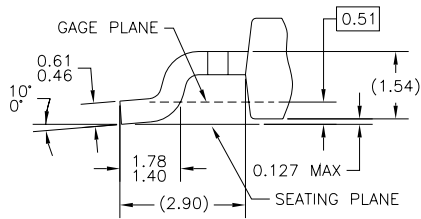
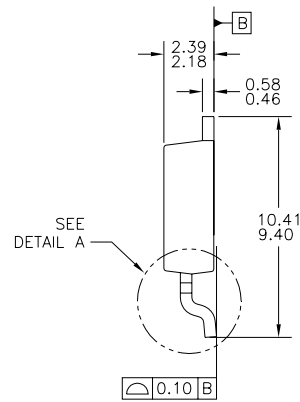
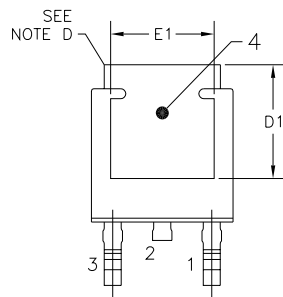


Mechanical Dimensions

D-PAK



LAND PATTERN RECOMMENDATION



DETAIL A
(ROTATED -90°)
SCALE: 12X

- NOTES: UNLESS OTHERWISE SPECIFIED
- A) ALL DIMENSIONS ARE IN MILLIMETERS.
 - B) THIS PACKAGE CONFORMS TO JEDEC, TO-252, ISSUE C, VARIATION AA & AB, DATED NOV. 1999.
 - C) DIMENSIONING AND TOLERANCING PER ASME Y14.5M-1994.
 - D) HEAT SINK TOP EDGE COULD BE IN CHAMFERED CORNERS OR EDGE PROTRUSION.
 - E) DIMENSIONS L3,D,E1&D1 TABLE:
- | | OPTION AA | OPTION AB |
|----|-----------|-----------|
| L3 | 0.89-1.27 | 1.52-2.03 |
| D | 5.97-6.22 | 5.33-5.59 |
| E1 | 4.32 MIN | 3.81 MIN |
| D1 | 5.21 MIN | 4.57 MIN |
- F) PRESENCE OF TRIMMED CENTER LEAD IS OPTIONAL.

Dimensions in Millimeters



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| Build it Now™ | F-PFS™ | Power-SPM™ | the power franchise |
| CorePLUS™ | FRFET® | PowerTrench® | TinyBoost™ |
| CorePOWER™ | Global Power Resource™ | Programmable Active Droop™ | TinyBuck™ |
| CROSSVOL™ | Green FPS™ | QFET® | TinyLogic® |
| CTL™ | Green FPS™ e-Series™ | QS™ | TINYOPTO™ |
| Current Transfer Logic™ | GTO™ | Quiet Series™ | TinyPower™ |
| EcoSPARK® | IntelliMAX™ | RapidConfigure™ | TinyPWM™ |
| EfficientMax™ | ISOPLANAR™ | Saving our world, 1mW at a time™ | SmartMax™ |
| EZSWITCH™ * | MegaBuck™ | SmartMax™ | TinyWire™ |
| EZ™ | MICROCOUPLER™ | SMART START™ | µSerDes™ |
| F® | MicroFET™ | SPM® | µSerDes™ |
| Fairchild® | MicroPak™ | STEALTH™ | UHC® |
| Fairchild Semiconductor® | MillerDrive™ | SuperFET™ | Ultra FRFET™ |
| FACT Quiet Series™ | MotionMax™ | SuperSOT™-3 | UniFET™ |
| FACT® | Motion-SPM™ | SuperSOT™-6 | VCX™ |
| FAST® | OPTOLOGIC® | SuperSOT™-8 | VisualMax™ |
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2. A critical component in any component of a life support, device, or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

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Definition of Terms

Datasheet Identification	Product Status	Definition
Advance Information	Formative / In Design	This datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
Preliminary	First Production	This datasheet contains preliminary data; supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve design.
No Identification Needed	Full Production	This datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve the design.
Obsolete	Not In Production	This datasheet contains specifications on a product that is discontinued by Fairchild Semiconductor. The datasheet is for reference information only.

Rev. I34